

N-Channel 250-V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
250	0.165 at $V_{GS} = 10$ V	18

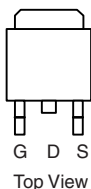
FEATURES

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- Low Thermal Resistance Package

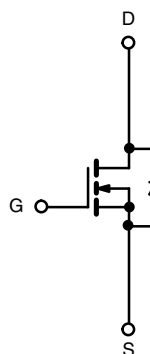


RoHS
COMPLIANT

TO-263



Ordering Information: SUM18N25-165-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	250	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	I_D	18	A
		10.4	
Pulsed Drain Current	I_{DM}	20	
Single Pulse Avalanche Current	I_{AS}	5	
Single Pulse Avalanche Energy ^a	E_{AS}	1.25	mJ
Maximum Power Dissipation ^a	P_D	150 ^b	W
		3.75	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	40	°C/W
Junction-to-Case (Drain)	R_{thJC}	1.0	

Notes:

a. Duty cycle ≤ 1 %.

b. See SOA curve for voltage derating.

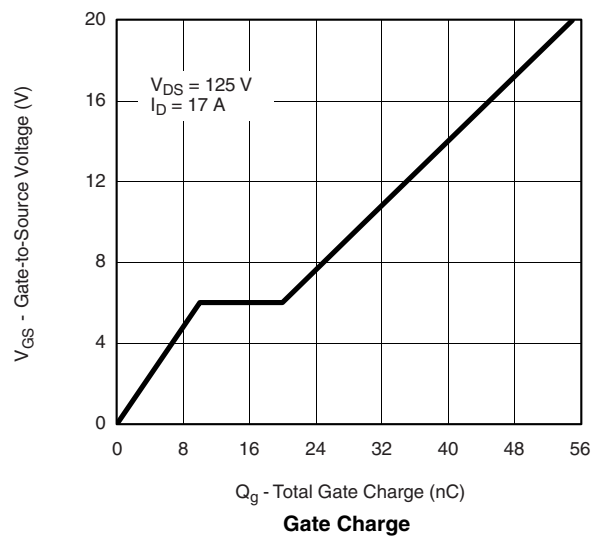
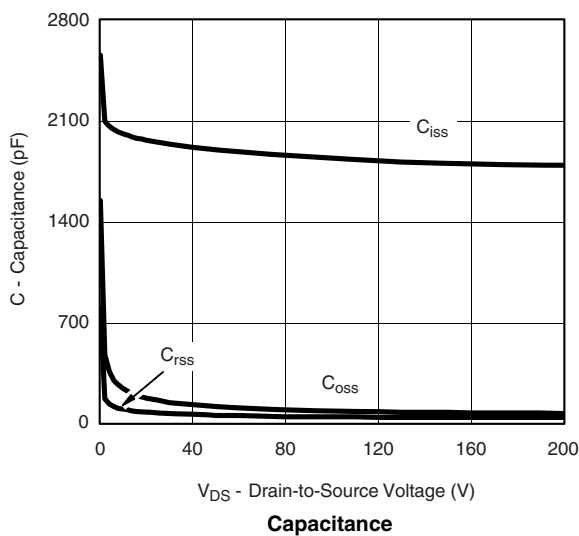
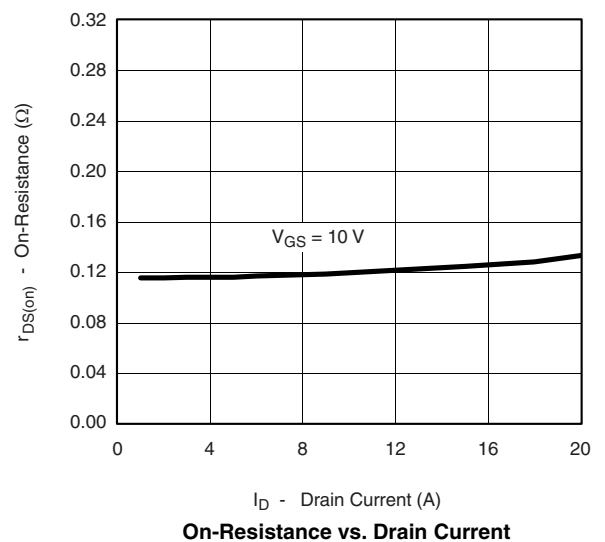
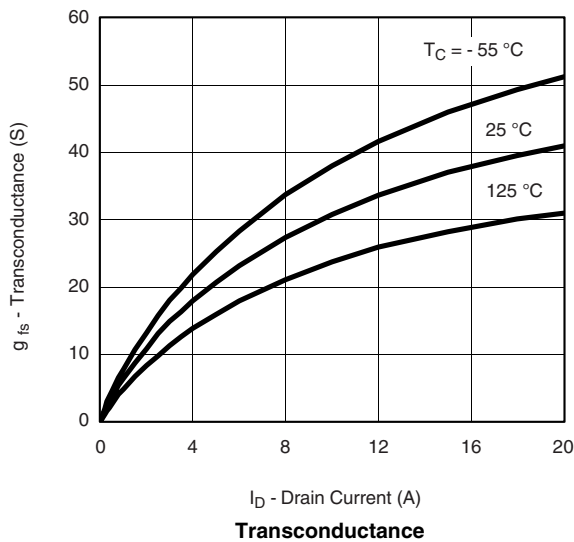
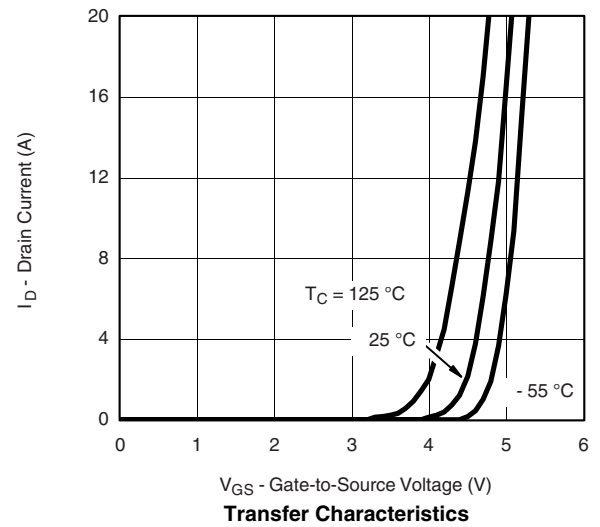
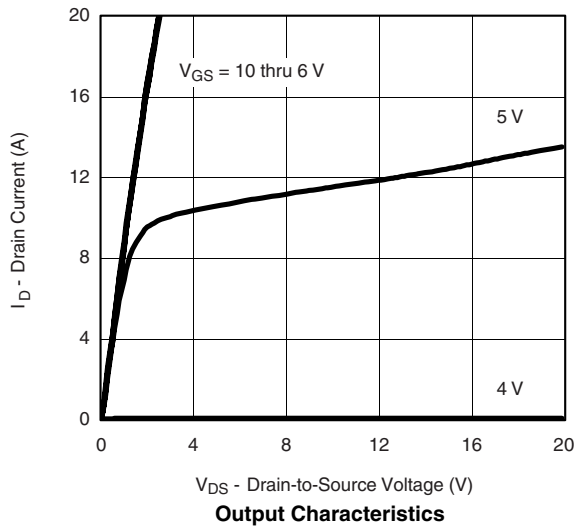
c. When Mounted on 1" square PCB (FR-4 material).

SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	250			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V			1	μA
		V _{DS} = 250 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 250 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 15 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 14 A		0.130	0.165	Ω
		V _{GS} = 10 V, I _D = 14 A, T _J = 125 °C			0.347	
		V _{GS} = 10 V, I _D = 14 A, T _J = 175 °C			0.462	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 18 A		36		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1950		pF
Output Capacitance	C _{oss}			160		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Q _g	V _{DS} = 125 V, V _{GS} = 10 V, I _D = 18 A		30	45	nC
Gate-Source Charge ^c	Q _{gs}			10		
Gate-Drain Charge ^c	Q _{gd}			10		
Gate Resistance	R _g			1.6		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 125 V, R _L = 7.0 Ω I _D ≅ 18 A, V _{GEN} = 10 V, R _g = 2.5 Ω		15	25	ns
Rise Time ^c	t _r			130	195	
Turn-Off Delay Time ^c	t _{d(off)}			30	45	
Fall Time ^c	t _f			100	150	
Source-Drain Diode Ratings and Characteristics T _C = 25 °C ^b						
Continuous Current	I _S				18	A
Pulsed Current	I _{SM}				20	
Forward Voltage ^a	V _{SD}	I _F = 18 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 18 A, di/dt = 100 A/μs		115	175	ns
Peak Reverse Recovery Charge	I _{RM(REC)}			10	15	A
Reverse Recovery Charge	Q _{rr}				0.58	1.3

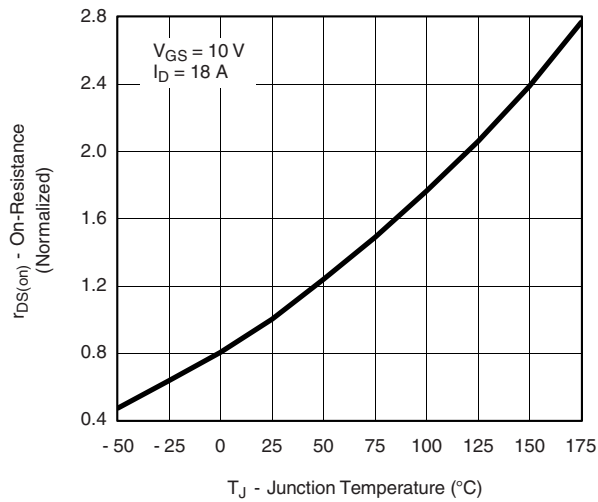
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

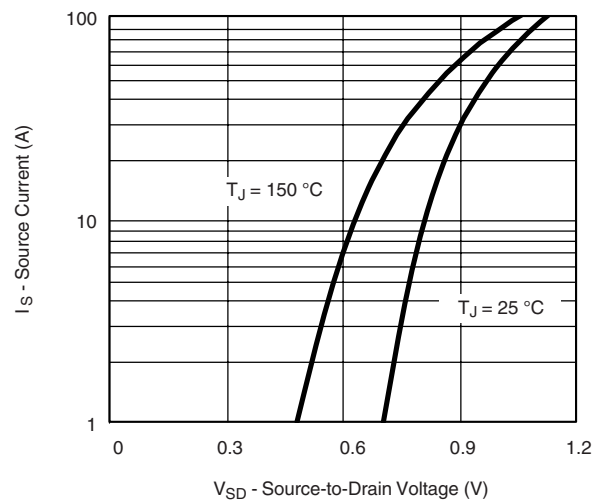
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


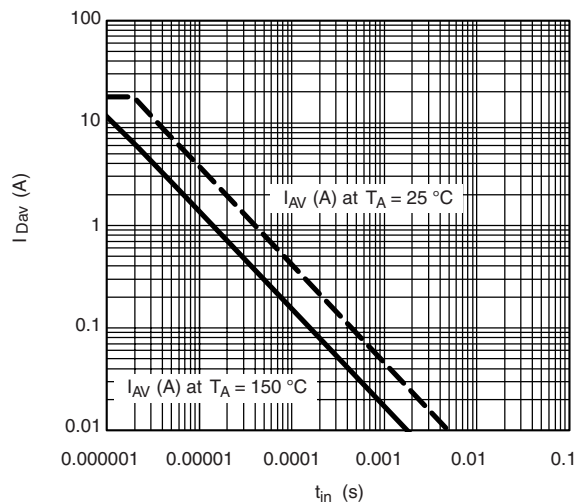
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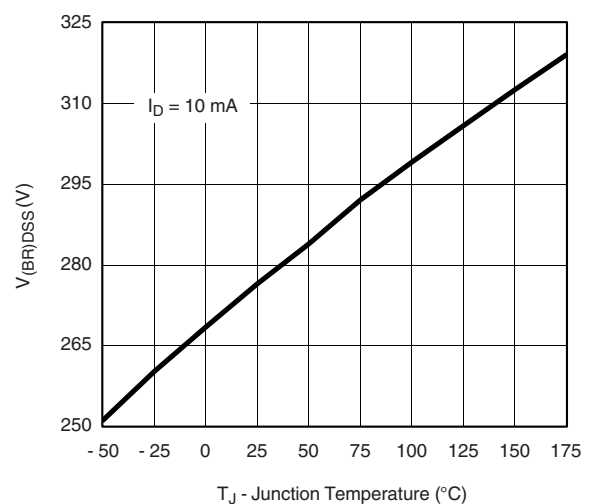
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

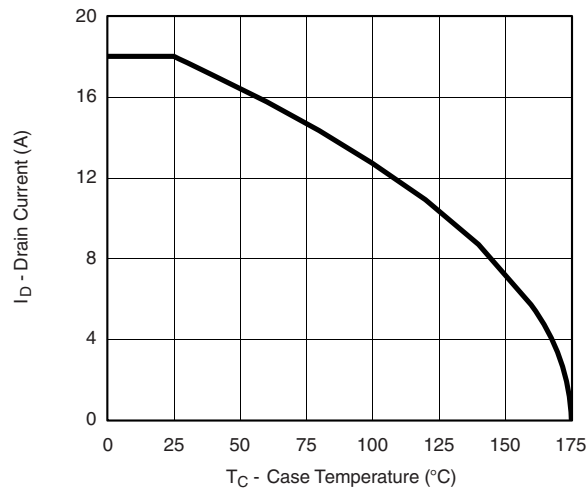


Avalanche Current vs. Time

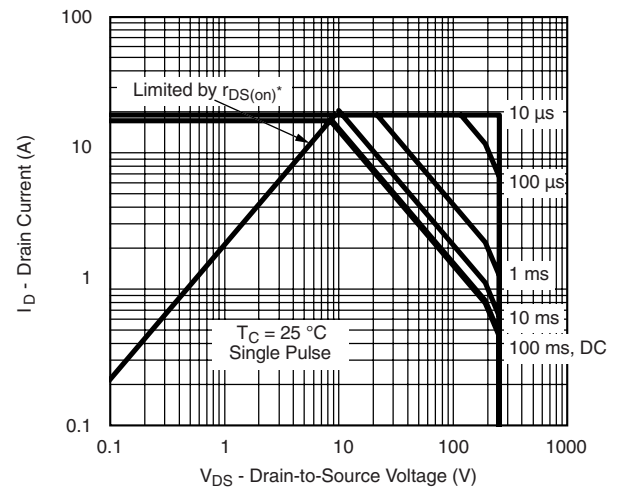


Drain Source Breakdown vs. Junction Temperature

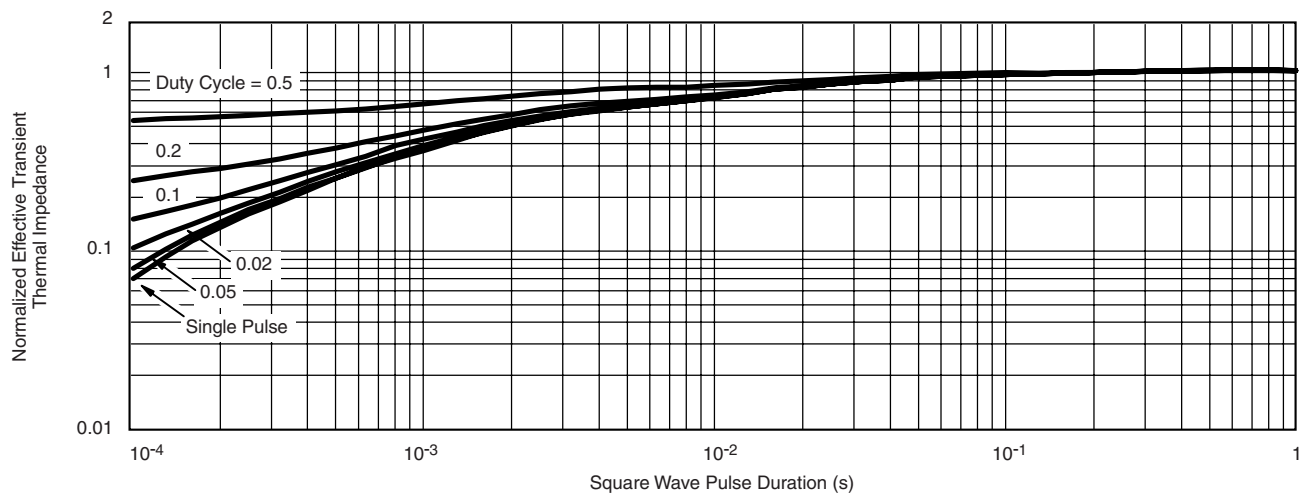
THERMAL RATINGS



Maximum Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

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